

- ★ Green Device Available
- ★ Super Low Gate Charge
- ★ Excellent Cdv/dt effect decline
- ★ Advanced high cell density Trench technology

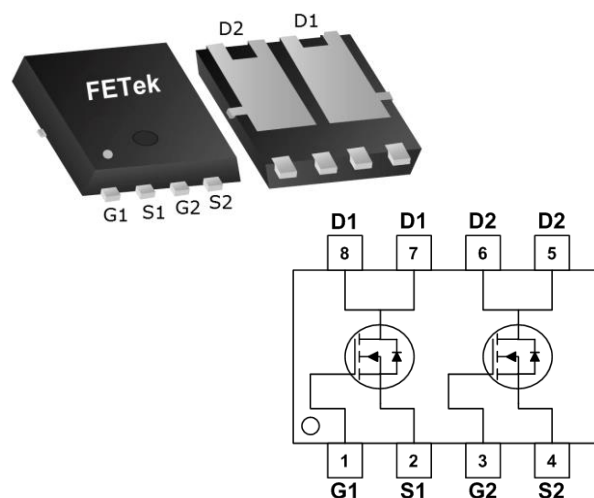
Product Summary


BVDSS	RDSON	ID
100V	290mΩ	4.9A

General Description

The FKBB0208 is the high cell density trenched N-ch MOSFETs, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The FKBB0208 meet the RoHS and Green Product requirement with full function reliability approved.

PRPAK3x3 Pin Configuration

Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V _{DS}	Drain-Source Voltage	100	V
V _{GS}	Gate-Source Voltage	±20	V
I _D @T _c =25°C	Continuous Drain Current, V _{GS} @ 10V ¹	4.9	A
I _D @T _c =70°C	Continuous Drain Current, V _{GS} @ 10V ¹	3.9	A
I _{DM}	Pulsed Drain Current ²	11	A
P _D @T _c =25°C	Total Power Dissipation ³	15.6	W
T _{STG}	Storage Temperature Range	-55 to 150	°C
T _J	Operating Junction Temperature Range	-55 to 150	°C

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
R _{θJA}	Thermal Resistance Junction-ambient ¹	---	80	°C/W
R _{θJC}	Thermal Resistance Junction-Case ¹	---	8	°C/W

**Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)**

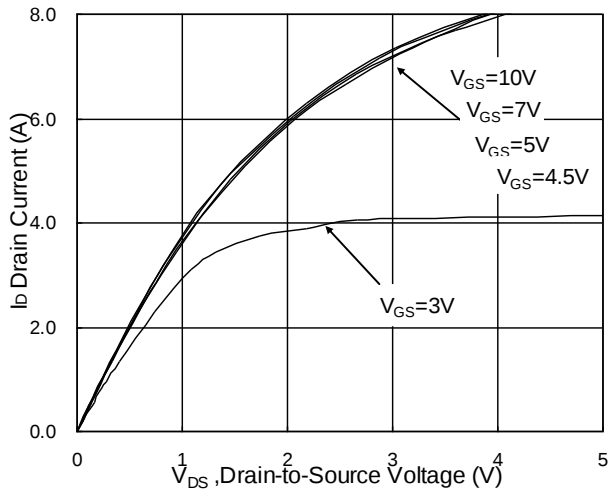
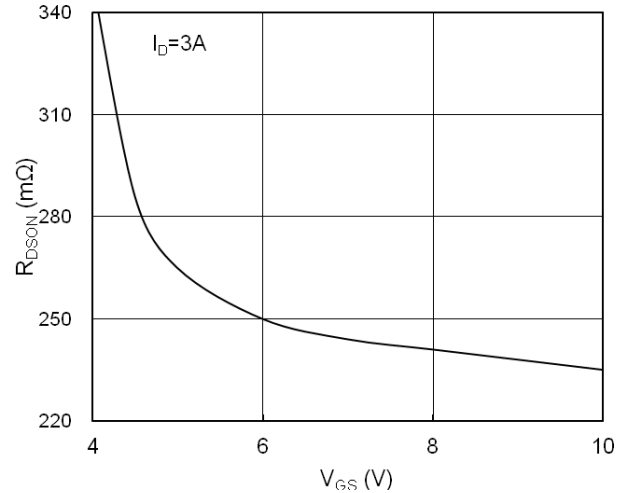
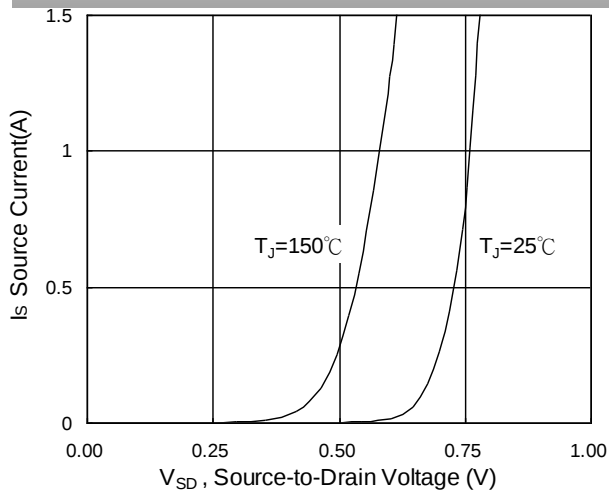
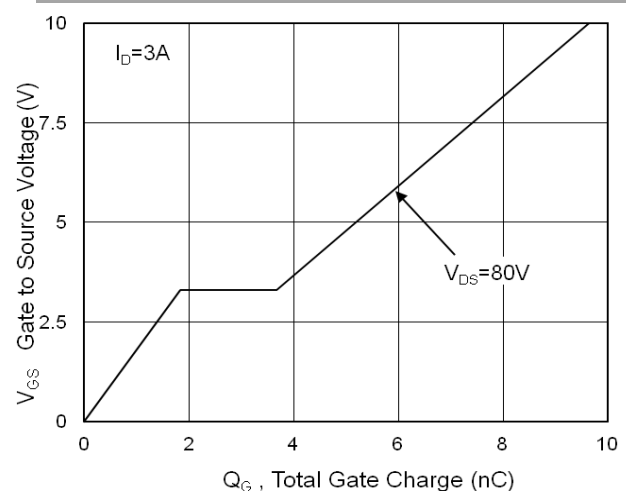
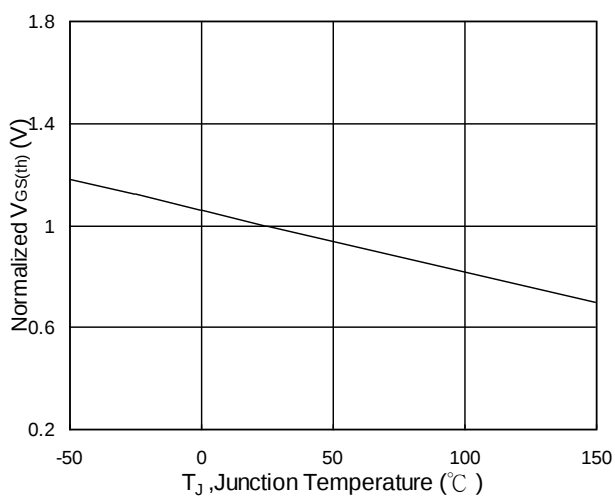
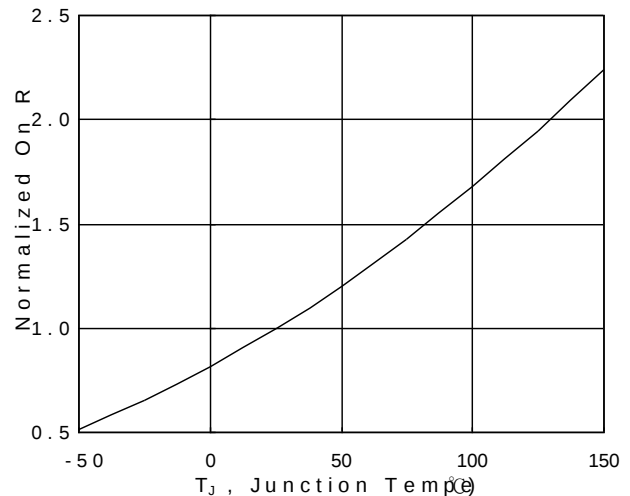
Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V$, $I_D=250\mu A$	100	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance ²	$V_{GS}=10V$, $I_D=3A$	---	260	290	$m\Omega$
		$V_{GS}=4.5V$, $I_D=3A$	---	270	320	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}$, $I_D=250\mu A$	1.0	---	3.0	V
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=80V$, $V_{GS}=0V$, $T_J=25^\circ\text{C}$	---	---	10	μA
		$V_{DS}=80V$, $V_{GS}=0V$, $T_J=55^\circ\text{C}$	---	---	100	
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V$, $V_{DS}=0V$	---	---	± 100	nA
g_{fs}	Forward Transconductance	$V_{DS}=5V$, $I_D=3A$	---	5.5	---	S
R_g	Gate Resistance	$V_{DS}=0V$, $V_{GS}=0V$, $f=1\text{MHz}$	---	2.5	---	Ω
Q_g	Total Gate Charge (4.5V)	$V_{DS}=80V$, $V_{GS}=10V$, $I_D=3A$	---	9.6	---	nC
Q_{gs}	Gate-Source Charge		---	1.83	---	
Q_{gd}	Gate-Drain Charge		---	1.85	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=50V$, $V_{GS}=10V$, $R_G=3.3\Omega$ $I_D=3A$	---	1.4	---	ns
T_r	Rise Time		---	30.6	---	
$T_{d(off)}$	Turn-Off Delay Time		---	11.2	---	
T_f	Fall Time		---	6	---	
C_{iss}	Input Capacitance	$V_{DS}=15V$, $V_{GS}=0V$, $f=1\text{MHz}$	---	508	---	pF
C_{oss}	Output Capacitance		---	29	---	
C_{rss}	Reverse Transfer Capacitance		---	16.4	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current ^{1,4}	$V_G=V_D=0V$, Force Current	---	---	4.9	A
I_{SM}	Pulsed Source Current ^{2,4}		---	---	11	A
V_{SD}	Diode Forward Voltage ²	$V_{GS}=0V$, $I_S=1A$, $T_J=25^\circ\text{C}$	---	---	1.2	V

Note :

1.The data tested by surface mounted on a 1 inch² FR-4 board with 20Z copper.2.The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$ 3.The power dissipation is limited by 150°C junction temperature4.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Typical Characteristics

Fig.1 Typical Output Characteristics

Fig.2 On-Resistance vs. Gate-Source

Fig.3 Forward Characteristics Of Reverse

Fig.4 Gate-Charge Characteristics

Fig.5 Normalized $V_{GS(th)}$ vs. T_J

Fig.6 Normalized $R_{DS(on)}$ vs. T_J

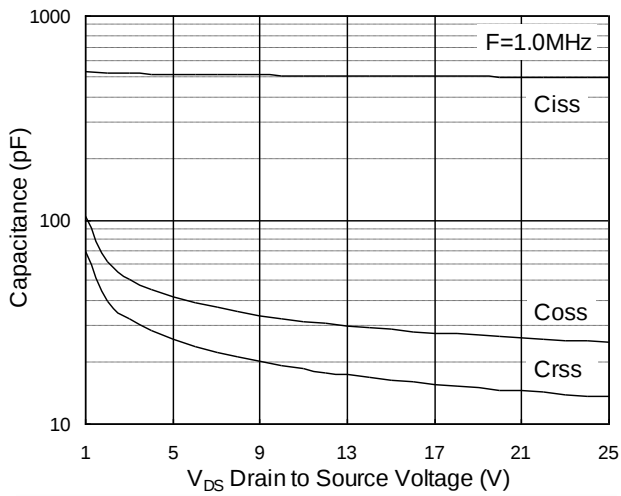


Fig.7 Capacitance

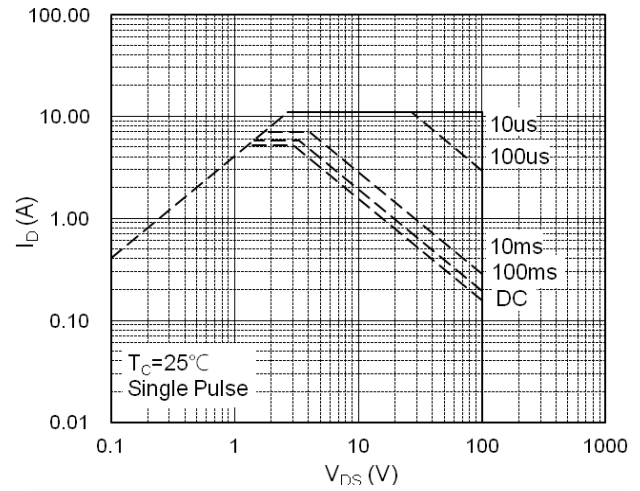


Fig.8 Safe Operating Area

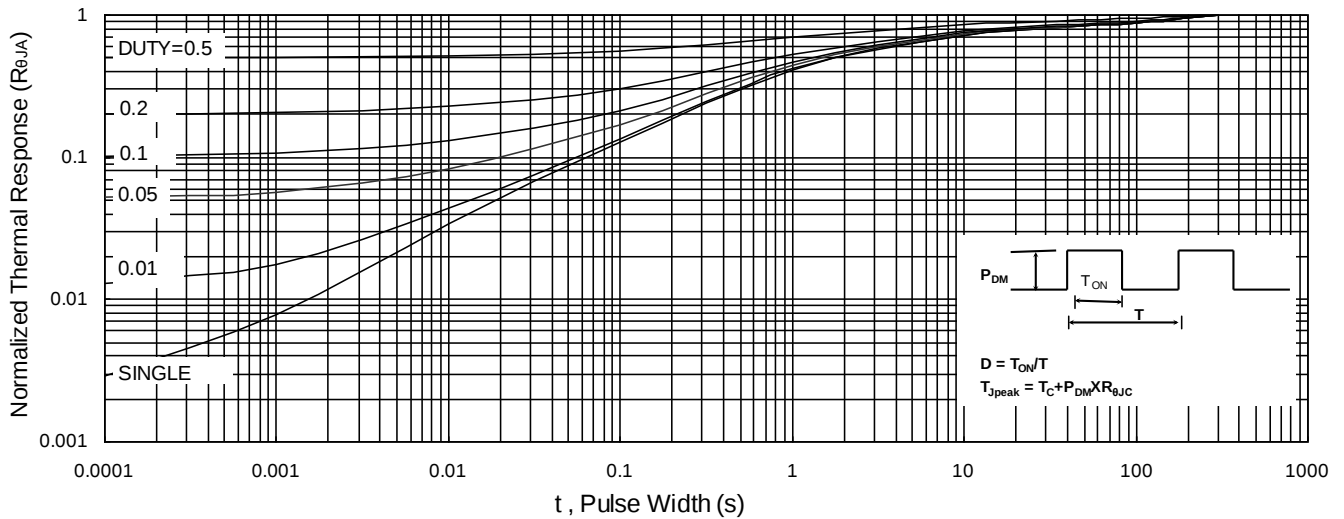


Fig.9 Normalized Maximum Transient Thermal Impedance

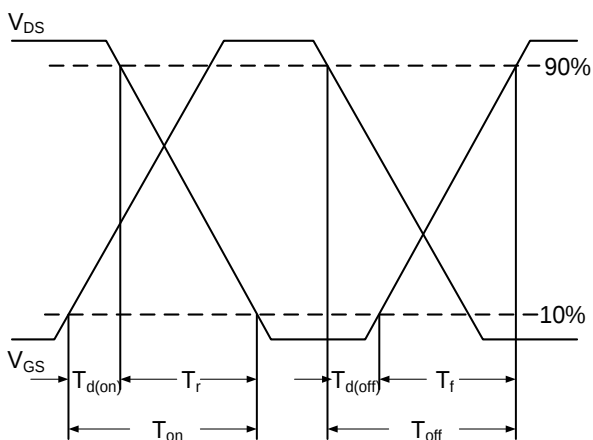


Fig.10 Switching Time Waveform

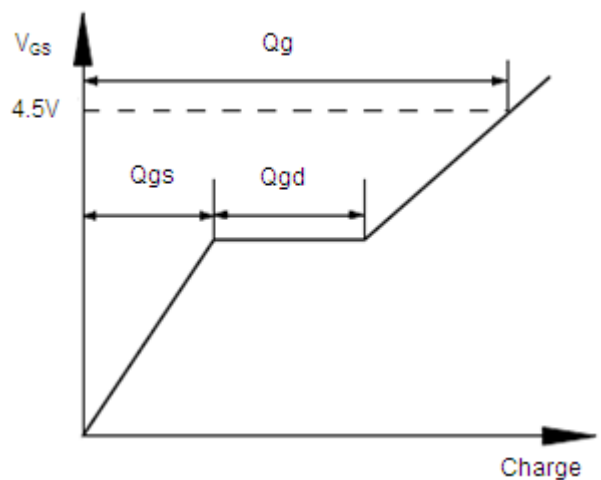


Fig.11 Gate Charge Waveform